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| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b> | Application No.      | 10/623,482          |                    |
|  | Filing Date          | July 18, 2003       |                    |
|  | First Named Inventor | Michael A. Todd     |                    |
|  | Art Unit             | 2812                |                    |
| (Multiple sheets used when necessary)                    |                      | Examiner            | Ron Everett Pompey |
| SHEET 1 OF 1   |                      | Attorney Docket No. | ASMEX.376A         |

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| NON PATENT LITERATURE DOCUMENTS |          |   |                |  |
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| Examiner Initials               | Cite No. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T <sup>1</sup> |  |
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\*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

T<sup>1</sup> - Place a check mark in this area when an English language Translation is attached.